

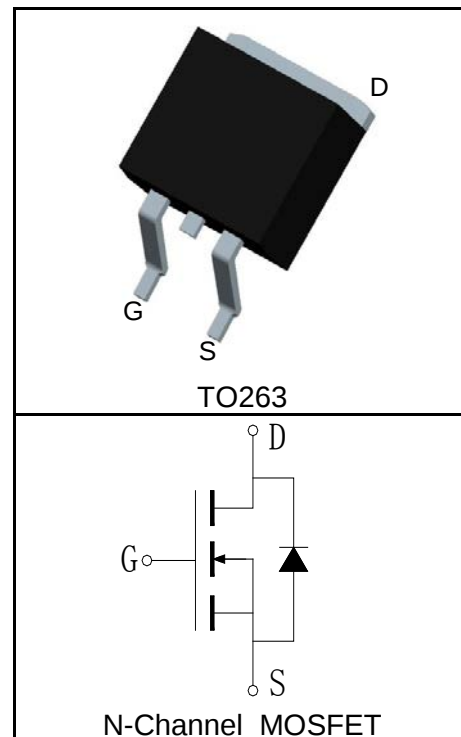
Features

- 150V/80A,
 $R_{DS(ON)} = 31m\Omega(Typ.)@V_{GS}=10V$
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available

Applications

- Automotive applications and a wide variety of other applications
- High Efficiency Synchronous in SMPS
- High Speed Power Switching

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	150	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ C$ 80	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C = 25^\circ C$ 300	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=10V$)	$T_C = 25^\circ C$ 80	A
		$T_C = 100^\circ C$ 60	
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$ 176	W
		$T_C = 100^\circ C$ 88	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.85	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ C/W$
Drain-Source Avalanche Ratings			
$E_{AS}^{③}$	Avalanche Energy, Single Pulsed	169	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

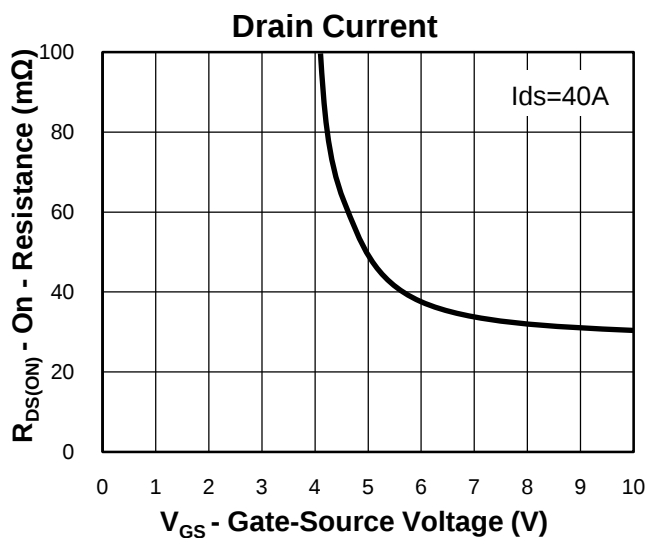
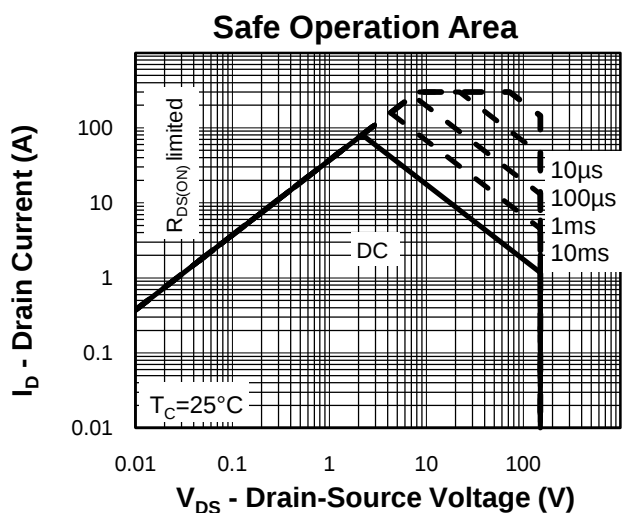
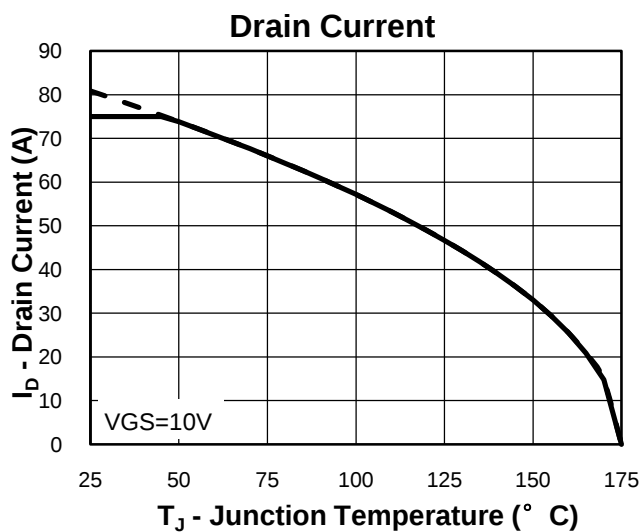
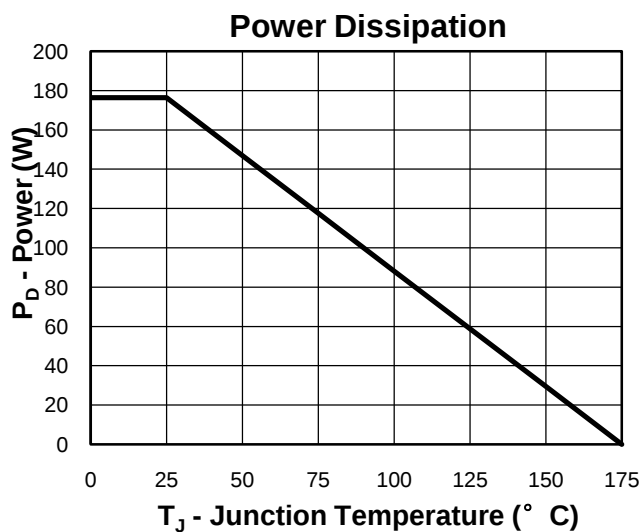
Symbol	Parameter	Test Condition	RU80N15S			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	150			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =150V, V _{GS} =0V			1	μA
			T _J =125°C		30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^④	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =40A		31	36	mΩ
Diode Characteristics						
V _{SD} ^④	Diode Forward Voltage	I _{SD} =40A, V _{GS} =0V			1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =40A, dI _{SD} /dt=100A/μs		68		ns
Q _{rr}	Reverse Recovery Charge			130		nC
Dynamic Characteristics ^⑤						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz		1		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz		3800		pF
C _{oss}	Output Capacitance			550		
C _{rss}	Reverse Transfer Capacitance			250		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =35V, R _L =35Ω, I _{DS} =1A, V _{GEN} =10V, R _G =10Ω		18		ns
t _r	Turn-on Rise Time			32		
t _{d(OFF)}	Turn-off Delay Time			80		
t _f	Turn-off Fall Time			56		
Gate Charge Characteristics ^⑤						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =40A		90		nC
Q _{gs}	Gate-Source Charge			25		
Q _{gd}	Gate-Drain Charge			30		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
 - ③ Limited by T_{Jmax} , $I_{AS}=26A$, $V_{DD}=48V$, $R_G=50\Omega$, Starting $T_J=25^{\circ}\text{C}$.
 - ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑤ Guaranteed by design, not subject to production testing.

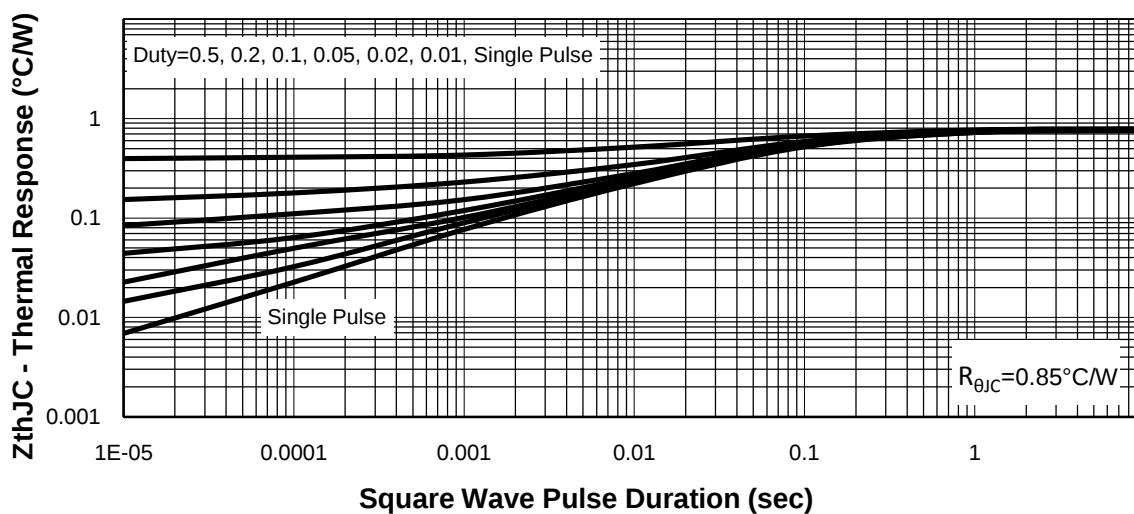
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU80N15S	RU80N15S	TO263	Tube	50	-	-

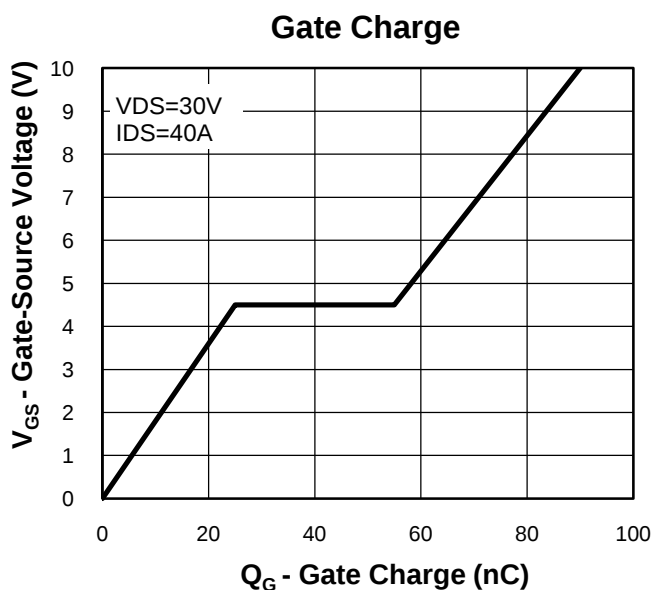
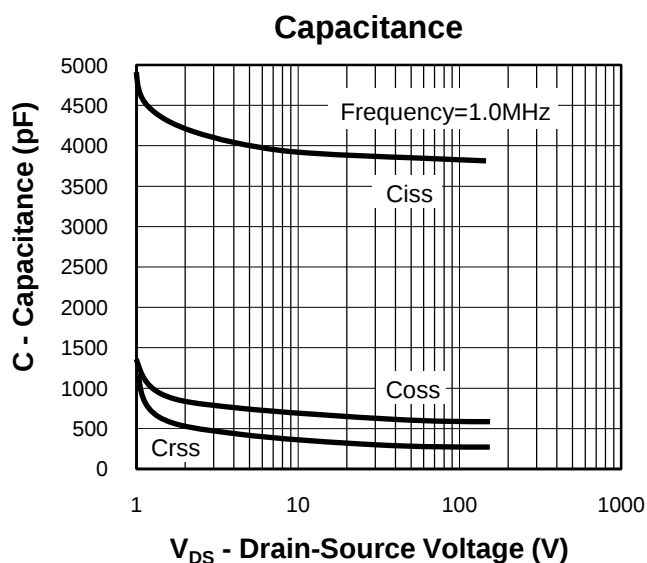
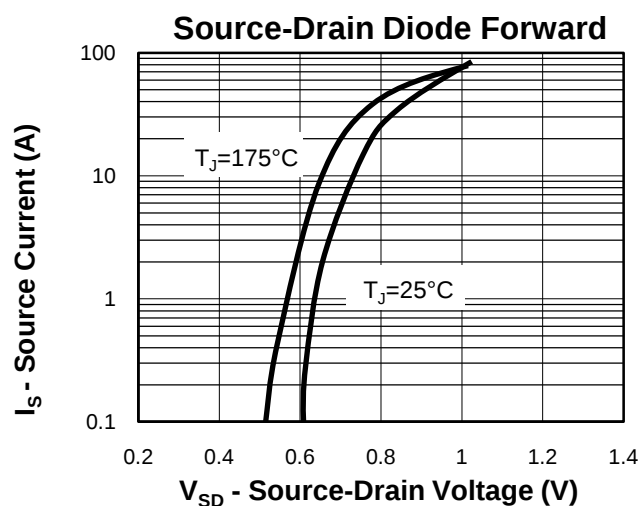
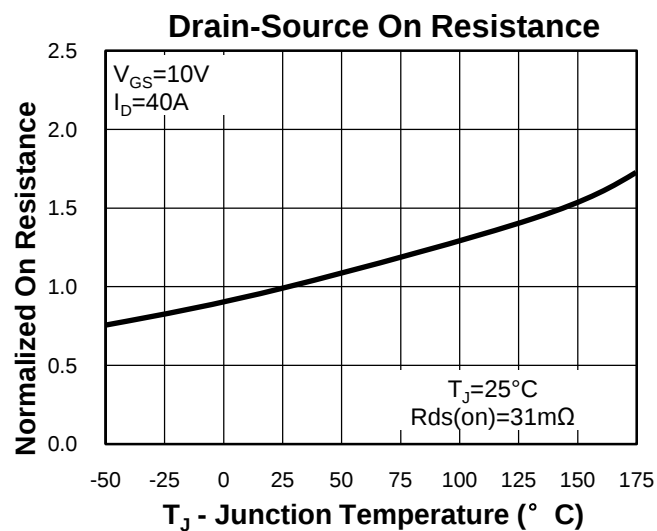
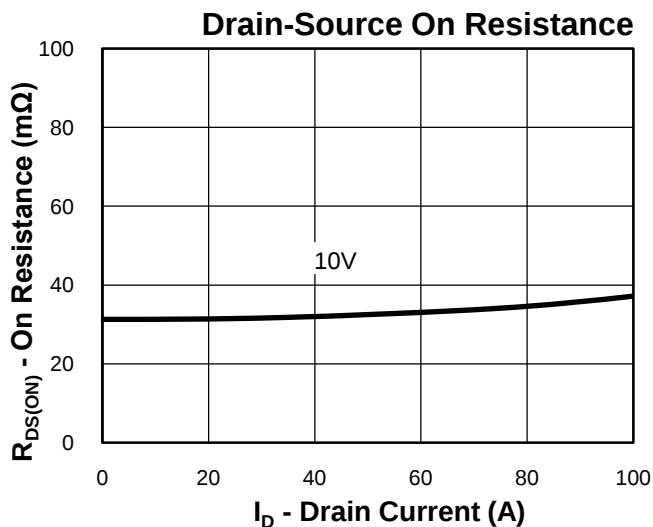
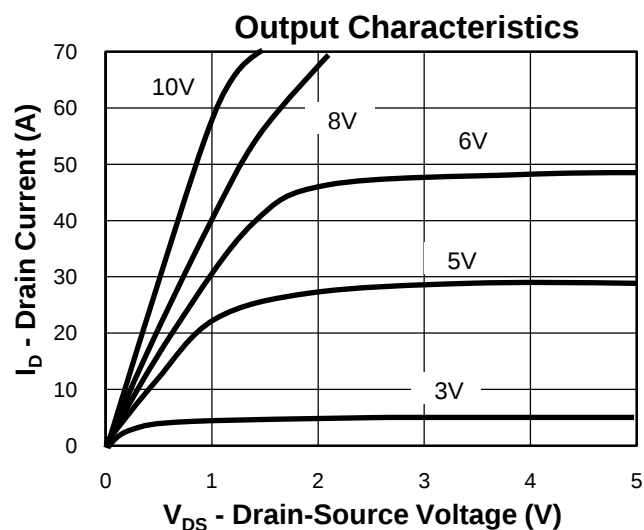
Typical Characteristics



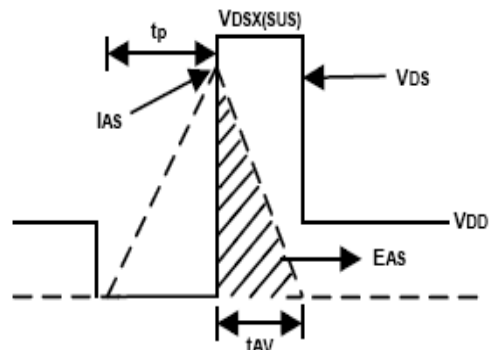
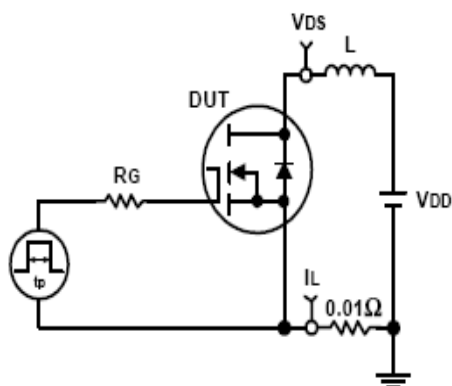
Thermal Transient Impedance



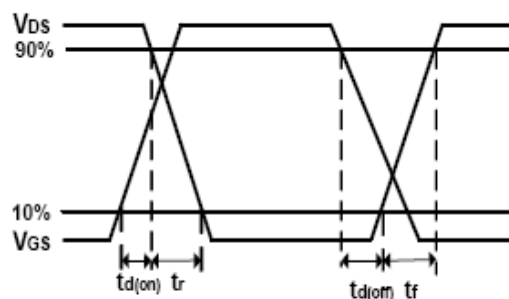
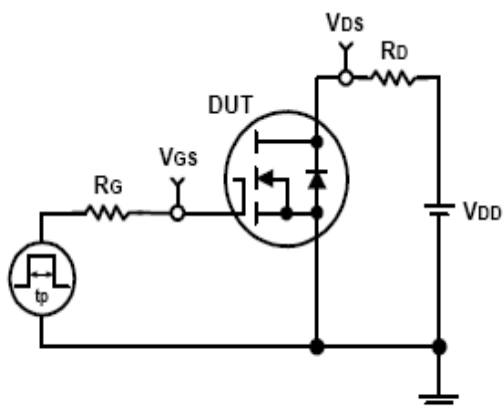
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Avalanche Test Circuit and Waveforms

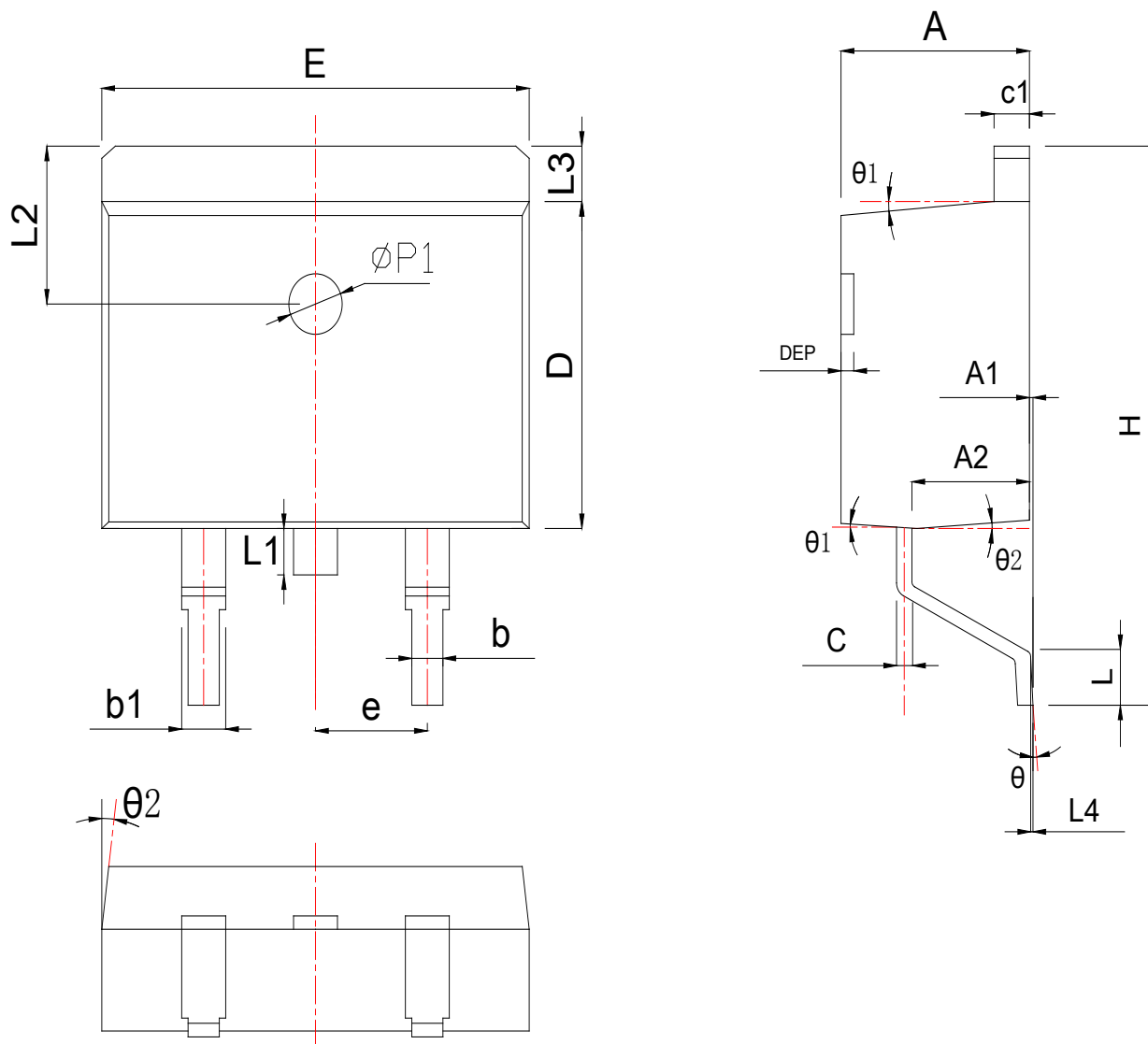


Switching Time Test Circuit and Waveforms



Package Information

TO263



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.55	4.70	0.173	0.179	0.185	L	2.00	2.30	2.60	0.079	0.091	0.102
A1	0.00	0.10	0.25	0.000	0.005	0.010	L3	1.17	1.29	1.40	0.046	0.051	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	*	*	1.70	*	*	0.067
b	0.77	*	0.90	0.030		0.035	L4	0.25 BSC			0.01 BSC		
b1	1.23	*	1.36	0.048		0.054	L2	2.50 REF			0.098 REF		
c	0.34	*	0.47	0.013		0.019	θ	0°	*	8°	0°	*	8°
c1	1.22	*	1.32	0.048		0.052	θ_1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.339	0.343	0.346	θ_2	1°	3°	5°	1°	3°	5°
E	10.00	10.13	10.26	0.394	0.399	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.100BSC			Φ_{p1}	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

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